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# AAP Gen 7 (TO-240AA) Power Modules Thyristor/Thyristor, 45 A, 60 A



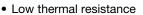
PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub>	45 A, 60 A					
Type	Modules - thyristor, standard					
Package	AAP Gen 7 (TO-240AA)					

#### **MECHANICAL DESCRIPTION**

The AAP Gen 7 (TO-240AA), new generation of APP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

### **FEATURES**

- High voltage
- Industrial standard package



- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **BENEFITS**

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- · Easy mounting on heatsink

#### **ELECTRICAL DESCRIPTION**

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VS-VSK.41	VS-VSK.56	UNITS			
I <sub>T(AV)</sub>	85 °C	45	60				
I <sub>T(RMS)</sub>		70	95	Δ.			
1	50 Hz	850	1200	А			
I <sub>TSM</sub>	60 Hz	890	1256				
I <sup>2</sup> t	50 Hz	3.61	7.20	kA <sup>2</sup> s			
1-1	60 Hz	3.30	6.57	KA-S			
$I^2\sqrt{t}$		36.1	72	kA²√s			
V <sub>RRM</sub>	Range	400 to 1600	400 to 1600	V			
T <sub>Stg</sub>		-40 to +125		°C			
T <sub>J</sub>		-40 to	°C				

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### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I <sub>RRM,</sub> I <sub>DRM</sub> AT 125 °C mA			
	04	400	500	400				
VS-VSK.41	08	800	900	800	15			
VS-VSK.56	12	1200	1300	1200	15			
	16	1600	1700	1600				

ON-STATE CONDUCTION	N						
PARAMETER	SYMBOL	TEST CONDITIONS			VS-VSK.41	VS-VSK.56	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	180° conduction T <sub>C</sub> = 85 °C	on, half sine wav	/e,	45	60	А
Maximum continuous RMS		DC			70	95	
on-state current	I <sub>T(RMS)</sub>	T <sub>C</sub>			82	81	°C
		t = 10 ms	No voltage		850	1200	
Maximum peak, one-cycle		t = 8.3 ms	reapplied	Sinusoidal half wave,	890	1256	Α
non-repetitive on-state current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	initial $T_{.1} = T_{.1}$ maximum	715	1000	_ A
		t = 8.3 ms	reapplied		750	1056	
		t = 10 ms	No voltage		3.61	7.20	kA <sup>2</sup> s
12. 6 . 6 .	l <sup>2</sup> t	t = 8.3 ms	reapplied		3.30	6.57	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	100 % V <sub>RRM</sub>	Initial $T_J = T_J$ maximum	2.56	5.10	
		t = 8.3 ms	reapplied		2.33	4.56	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t <sup>(1)</sup>	$t = 0.1 \text{ ms to } 1000 \text{ ms}$ $T_J = T_J \text{ maximum}$		e reapplied	36.1	72	kA <sup>2</sup> √s
Maximum value of threshold	(0)	Low level (3)	T T		1.08	0.91	.,
voltage	V <sub>T(TO)</sub> (2)	High level (4)	$T_J = T_J \text{ maxir}$	num	1.12	1.02	V
Maximum value of on-state	(2)	Low level (3)	T T		4.7	4.27	0
slope resistance	r <sub>t</sub> <sup>(2)</sup>	High level (4)	$T_{J} = T_{J} \text{ maximum}$		4.5	3.77	mΩ
Maximum on-state voltage drop	$V_{TM}$	$I_{TM} = \pi \times I_{T(AV)}$	x I <sub>T(AV)</sub> T <sub>J</sub> = 25 °C		1.81	1.7	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$\begin{split} T_J = 25~^{\circ}\text{C, from 0.67 V}_{DRM}, \\ I_{TM} = \pi~\text{x I}_{T(AV)}, ~I_g = 500~\text{mA}, ~t_r < 0.5~\mu\text{s}, ~t_p > 6~\mu\text{s} \end{split}$			15	50	A/µs
Maximum holding current	I <sub>H</sub>	T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load, gate open circuit			20	00	mA
Maximum latching current	ΙL	$T_J = 25 ^{\circ}\text{C}$ , and	ode supply = 6	/, resistive load	40	00	

#### Notes

<sup>(1)</sup>  $I^2t$  for time  $t_x = I^2\sqrt{t} \times \sqrt{t_x}$ 

<sup>&</sup>lt;sup>(2)</sup> Average power =  $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$ 

 $<sup>^{(3)}</sup>$  16.7 % x  $\pi$  x  $I_{AV} < I < \pi$  x  $I_{AV}$ 

 $<sup>^{(4)}</sup>$   $I > \pi \times I_{AV}$ 



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TRIGGERING							
PARAMETER	SYMBOL	TEST CO	ONDITIONS	VS-VSK.41	VS-VSK.56	UNITS	
Maximum peak gate power	$P_{GM}$			1	0	W	
Maximum average gate power	P <sub>G(AV)</sub>			2	.5	VV	
Maximum peak gate current	I <sub>GM</sub>			2	.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>			1	0		
	V <sub>GT</sub>	T <sub>J</sub> = - 40 °C	Anode supply = 6 V resistive load	4	.0	V	
Maximum gate voltage required to trigger		T <sub>J</sub> = 25 °C		2	.5	v	
		T <sub>J</sub> = 125 °C		1	.7		
		T <sub>J</sub> = - 40 °C		2	70		
Maximum gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	1	50	mA	
		T <sub>J</sub> = 125 °C	resistive load	8	0		
Maximum gate voltage that will not trigger	$V_{GD}$	T <sub>J</sub> = 125 °C, rated V <sub>DRM</sub> applied		0.	25	V	
Maximum gate current that will not trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, rated	V <sub>DRM</sub> applied	(	6	mA	

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VS-VSK.41	VS-VSK.56	UNITS		
Maximum peak reverse and off-state leakage current at V <sub>RRM</sub> , V <sub>DRM</sub>	I <sub>RRM,</sub> I <sub>DRM</sub>	T <sub>J</sub> = 125 °C, gate open circuit	15		mA		
I Maximum RMS insulation voltage I V <sub>INS</sub> I 50 Hz		3000 ( 3600	,	V			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 125$ °C, linear to 0.67 $V_{DRM}$	10	00	V/µs		

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL TEST CONDITIONS VS		VS-VSK.41	VS-VSK.56	UNITS	
Junction operating and storag temperature range	е	T <sub>J</sub> , T <sub>Stg</sub>		-40 to	+125	°C	
Maximum internal thermal resi junction to case per leg	stance,	R <sub>thJC</sub>	DC operation	0.44	0.35	°C ///	
Typical thermal resistance, case to heatsink per module	•		Mounting surface flat, smooth and greased	0.1		°C/W	
	to heatsink		A mounting compound is recommended and the torque should be rechecked after	4	4		
Mounting torque ± 10 %	busbar		a period of 3 hours to allow for the spread of the compound.	;	3	Nm	
Approximate weight				7	'5	g	
Approximate weight				2	.7	oz.	
Case style			JEDEC®	AAP G	ien 7 (TO-240	AA)	

△R CONDUCTION PER JUNCTION											
DEVICES	SINE HALF WAVE CONDUCTION				N	RECTANGULAR WAVE CONDUCTION				ON	LIMITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.41	0.110	0.131	0.17	0.23	0.342	0.085	0.138	0.177	0.235	0.345	°C/W
VSK.56	0.088	0.104	0.134	0.184	0.273	0.07	0.111	0.143	0.189	0.275	]

### Note

Table shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

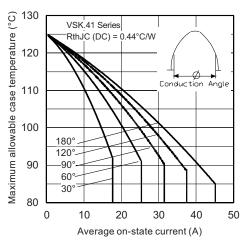


Fig. 1 - Current Ratings Characteristics

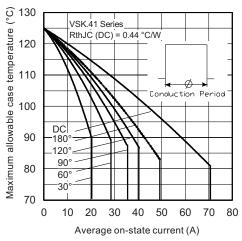


Fig. 2 - Current Ratings Characteristics

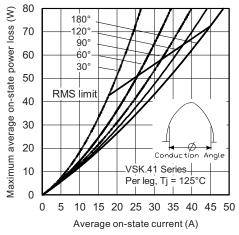


Fig. 3 - On-State Power Loss Characteristics

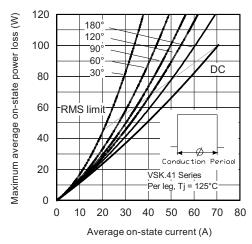
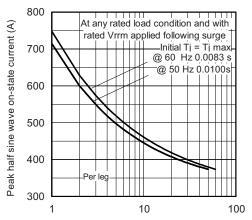


Fig. 4 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

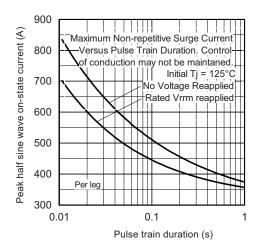


Fig. 6 - Maximum Non-Repetitive Surge Current

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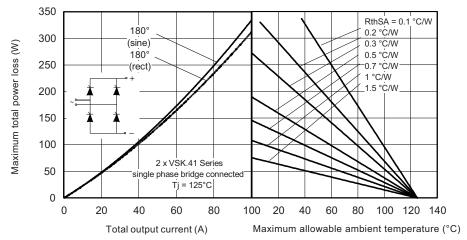


Fig. 7 - On-State Power Loss Characteristics

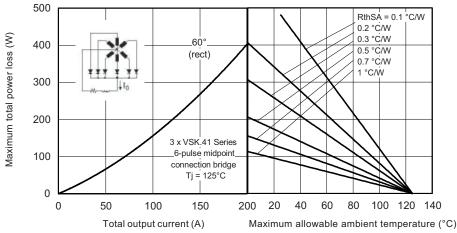


Fig. 8 - On-State Power Loss Characteristics

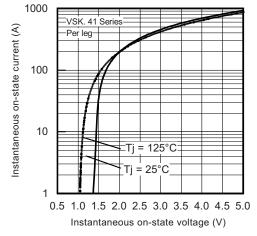


Fig. 9 - On-State Voltage Characteristics

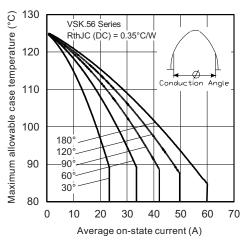


Fig. 10 - Current Ratings Characteristics

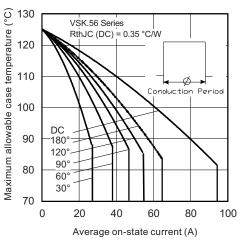


Fig. 11 - Current Ratings Characteristics

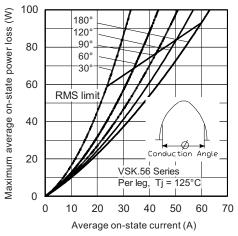


Fig. 12 - On-State Power Loss Characteristics

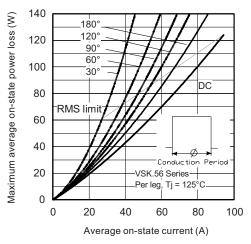
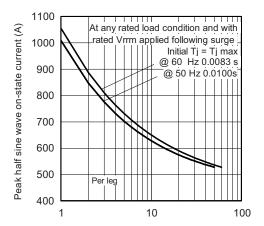


Fig. 13 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 14 - Maximum Non-Repetitive Surge Current

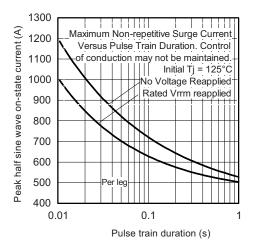


Fig. 15 - Maximum Non-Repetitive Surge Current

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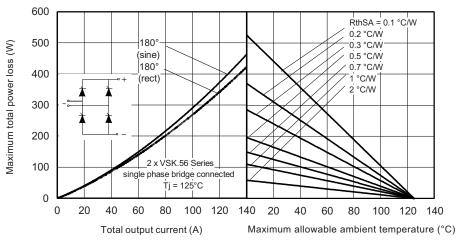


Fig. 16 - On-State Power Loss Characteristics

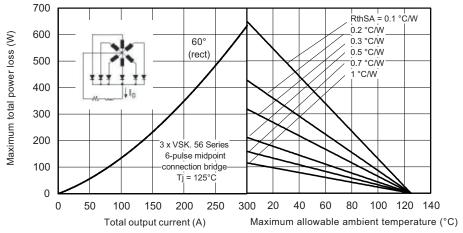


Fig. 17 - On-State Power Loss Characteristics

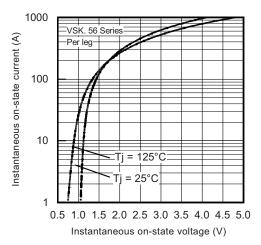


Fig. 18 - On-State Voltage Characteristics

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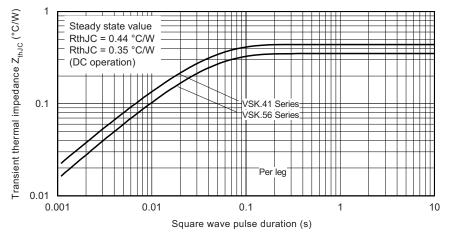


Fig. 19 - Thermal Impedance Z<sub>thJC</sub> Characteristics

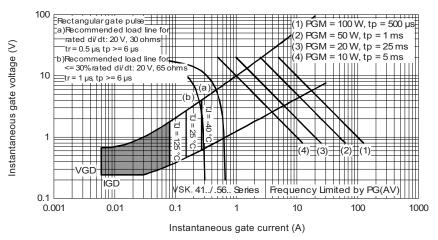
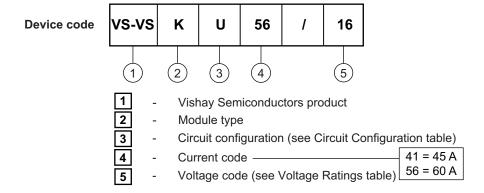


Fig. 20 - Gate Characteristics

### **ORDERING INFORMATION TABLE**



#### Note

• To order the optional hardware go to www.vishav.com/doc?95172

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CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs common cathodes	U	VSKU  (1)  1  2  (2)  (3)  (3)  (4) (5) (7) (6)
Two SCRs common anodes	V	VSKV  (1)  1  (2)  (3)  (3)  (3)  (4) (5) (7) (6)

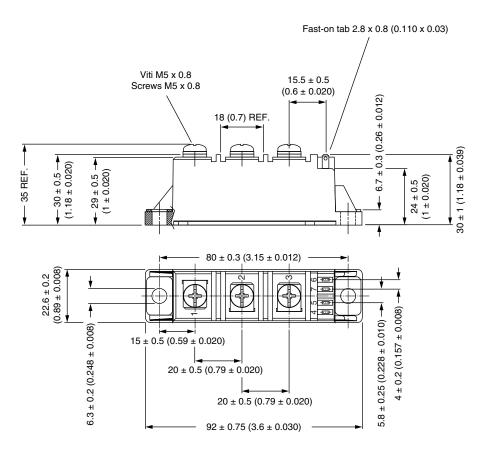
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95368			



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# **ADD-A-PAK Generation VII - Thyristor**

## **DIMENSIONS** in millimeters (inches)





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